

## 700V GaN Power Transistor

## **Description**

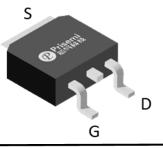
Product Summary					
V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)(Typ)$	I <sub>D</sub> (A)			
700	320	6			

### **Feature**

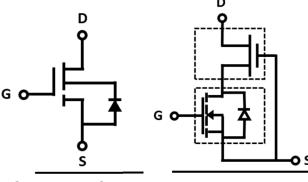
- > Easy to use, compatible with standard gate drivers
- $\succ$  Excellent Q<sub>G</sub> x R<sub>DS(on)</sub> figure of merit (FOM)
- ightharpoonup Low  $\mathbf{Q}_{\mathrm{RR}}$ , no free-wheeling diode required
- Low switching loss
- > RoHS compliant and Halogen-free

## **Applications**

- ➤ High efficiency power supplies
- > Telecom and datacom
- > Automotive
- Servo motors



TO-252 (Top View)



Schematic Symbol

Cascode Device Structure

## Absolute maximum rating@25°C

Parameter	Symbol	Rating	Unit		
Drain-Source Voltage		V <sub>DS</sub>	700	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
Transient Drain-Source Voltage <sup>1)</sup>		V <sub>TDS</sub>	800	V	
Continuo Dunio Coment	T <sub>C</sub> =25°C		6	Α	
Continuous Drain Current	T <sub>C</sub> =100°C	l <sub>D</sub>	3.7		
Duland Dunin Comment (Dulan Midth: 1000)	T <sub>C</sub> =25°C		25	Α	
Pulsed Drain Current (Pulse Width: 100μs)	T <sub>C</sub> =150°C	I <sub>DM</sub>	18		
Power Dissipation		P <sub>D</sub>	20	W	
Soldering Peak Temperature		T <sub>CSOLD</sub>	260	°C	
Operating Junction and Storage Temperature		$T_{J_{i}}T_{STG}$	-55 to 150	°C	

## **Thermal Resistance**

Parameter	Symbol	Min	Тур	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	6.2	-	°C/W
Thermal Resistance, Junction-to-Ambient <sup>2)</sup>	R <sub>eJA</sub>	-	50	-	°C/W

# Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Units	
Statistic Characteristics								
Maximum Drain-Source Voltage	V <sub>DS-Max</sub>	V <sub>GS</sub> = 0V		700	-	-	V	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS} = 0V, I_{D} = 250\mu A$		-	1000	-	V	
Zone Cote Veltere Duein Comment		V <sub>DS</sub> =700V, V <sub>GS</sub> =0V	T <sub>J</sub> =25°C	-	4	15		
Zero Gate Voltage Drain Current	l <sub>DSS</sub>		T <sub>J</sub> =150°C	-	30	-	- μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$		-	-	±150	nA	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$	I <sub>D</sub> = 500μA	1.1	1.8	2.5	V	
Dunin Course On State Desigtance 3)		V <sub>cs</sub> =8V.	T <sub>J</sub> =25°C	-	320	400	mΩ	
Drain-Source On-State Resistance <sup>3)</sup>	$R_{DS(ON)}$	I <sub>D</sub> =4A	T <sub>J</sub> =150°C	-	640	-		
Dynamic Characteristics								
Input Capacitance	C <sub>lss</sub>	$V_{DS} = 400V, V_{GS} = 0V,$ $f = 1MHz$		-	274	-	pF	
Output Capacitance	C <sub>oss</sub>			-	12.6	-		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	0.6	-		
Effective Output Capacitance, Energy Related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0-400V		-	18.4	-		
Effective Output Capacitance, Time Related	C <sub>o(tr)</sub>			-	55.4	-	pF	
Output Charge	Q <sub>oss</sub>			-	22.1	-	nC	
Turn-on Delay Time	t <sub>d(on)</sub>			-	20	-		
Turn-on Rise Time	t <sub>r</sub>	$V_{DS} = 400V, I_{D} = 4A,$		-	12	-		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS} = 0.12V, R_G = 47\Omega$		-	72	-	ns	
Turn-Off Fall Time	t <sub>f</sub>			-	12	-		
Total Gate Charge	$Q_g$			-	5.5	-		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 400V, I_{D} = 6A,$ $V_{GS} = 0-8V$		-	1.1	-	nC	
Gate-Drain Charge	$Q_{\rm gd}$			-	2.5	-		
Reverse Diode Characteristics								
		V <sub>GS</sub> =0V	′, I <sub>S</sub> =3A	-	1.5	-		
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,	T <sub>J</sub> =25°C	-	2.2	-	V	
		I <sub>S</sub> =6A	T <sub>J</sub> =150°C	-	3.3	-		
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =6A,		-	14.2	-	ns	
Reverse Recovery Charge	harge $V_{DD}$ =400V, di/dt=1000A/µs			-	22.1	-	μC	

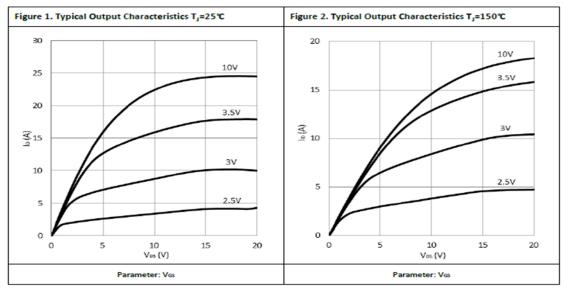
### Notes:

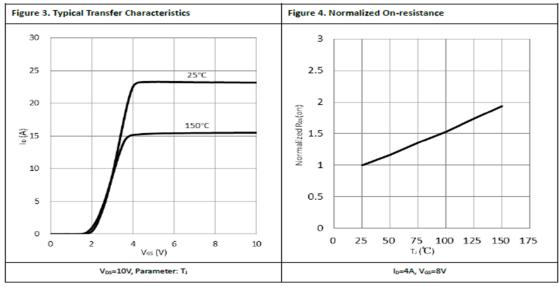
<sup>1.</sup> Off-state spike duty cycle < 0.01, spike duration < 2μs

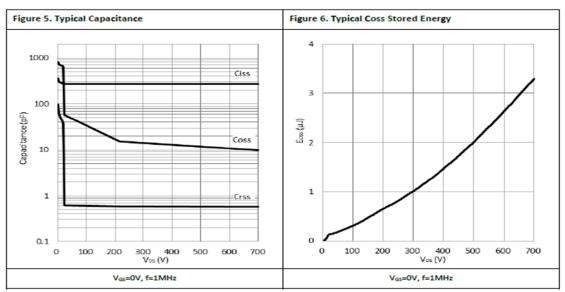
<sup>2.</sup> Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70µm thickness)

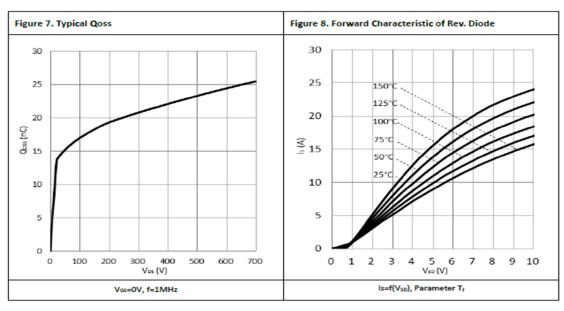
<sup>3.</sup> Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

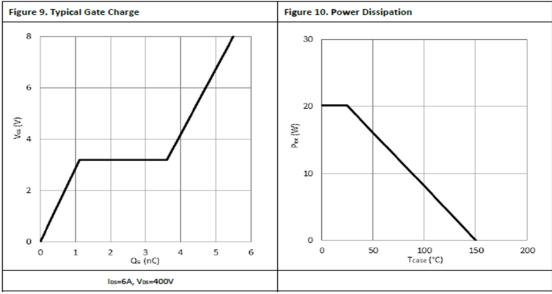
# **Typical Characteristics**

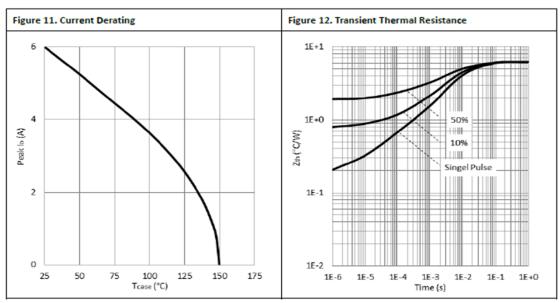


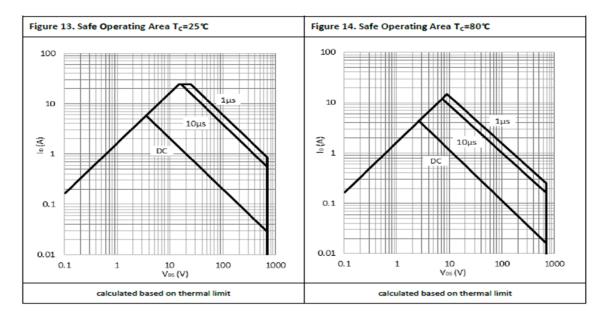




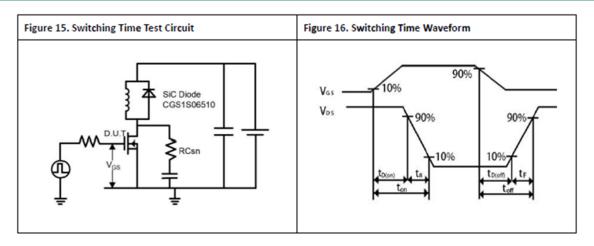


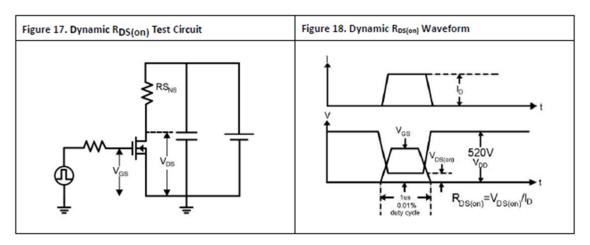


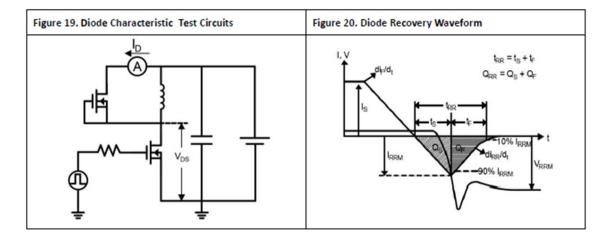




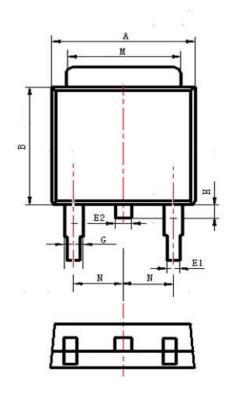
# **Test Circuits and Waveforms**

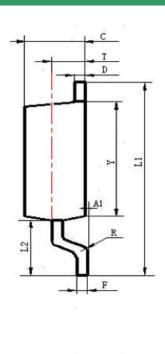






# **Product Dimension (TO-252)**





单位:mm

SYMBOL	Millimeter				
STWIBUL	Min Nom		Max		
А	6.30	6.60	6.90		
A1	0	0.80	0.16		
В	5.70	6.00	6.30		
С	2.10	2.30	2.50		
D	0.30	0.60	0.90		
E1	0.60	0.75	0.90		
F	0.30	0.45	0.60		
G	0.70	0.95	1.20		
L1	9.30	9.90	10.50		
L2	2.50	2.80	3.10		
Н	0.40	0.70	1.05		
М	4.90	5.30	5.60		
N	2.09	2.29	2.49		

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